

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a base substrate, an insulating film formed on the substrate, an undoped first and lattice-relaxed semiconductor layer formed on the insulating film, a second semiconductor layer having a tensile strain and formed on the first semiconductor layer, and a MISFET formed on the second semiconductor layer. Since the MISFET is formed in a strained Si layer, electrons are prevented from scattering in a channel region, improving the electron mobility. Furthermore, since the MISFET is formed in a thin SOI layer having a thickness of 100 nm or less, it is possible to reduce a parasitic capacitance in addition to the improvement of the electron mobility. As a result, the MISFET excellent in drivability can be obtained.